

**Amendments to the Specification:**

Please replace the title as follows:

~~SUBSTRATE TREATMENT APPARATUS, SUBSTRATE HOLDING DEVICE, AND~~  
~~SEMICONDUCTOR DEVICE MANUFACTURING METHOD~~  
SUBSTRATE PROCESSING APPARATUS, SUBSTRATE HOLDER, AND  
MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

Please replace the paragraph beginning on page 32, line 8 to line 20, with the following rewritten paragraph:

Note that film-forming conditions such as a gas type, a gas amount, a pressure, a temperature, and a time at the time of performing the evaluation are silane (~~SiH<sub>4</sub>~~)(SiH<sub>4</sub>) of 400 cc, phosphine (PH<sub>3</sub>) of 50 cc, the pressure at 300 Pa, the temperature in the processing chamber at 530°C, and the film-forming time (deposition time) for 30 min for a DPOLY film (doped polysilicon film). The evaluation shows the results when the distance La between the ring-like plate 13 and the wafer 200 in the portion where the support column is not present, which is shown in FIG. 8(a), is equal to 4 mm, and when the distance Lb between the support column 15 and the wafer 200 in the portion where the support column 15 is present, which is shown in FIG. 8(b), is equal to 8.5 mm.

Please replace the paragraph beginning on page 35, line 16 to line 27, with the following rewritten paragraph:

Moreover, in the conventional holder boat, the support claw portions ~~14-34~~ and each wafer have been brought into surface contact with each other, and sliding therebetween and the like when the wafer is inserted has caused the generation of the particles. Moreover, in the case of the CVD processing and the like, since the surface contact has been brought in the

contact portions of the support claw portions ~~14-34~~ with the wafer, it has been impossible to form the film on the back surface of the wafer. Therefore, a distortion owing to heat has occurred between the portion subjected to the film forming and the portion that is not subjected to the film forming on the back surface of the wafer, causing exfoliation of the film.

Please replace the paragraph beginning on page 35, line 28 to page 36, line 11 with the following rewritten paragraph:

In terms of this point, in this embodiment, as shown in FIG. 5, the fixing angle of each columnar wafer support portion 16 is set parallel to the wafer, and the tip of the wafer support portion 16 is rounded or chamfered to make the contact surface into a line, and accordingly, the particles generated owing to the sliding can be reduced to a great extent. Moreover, since the contact portion of the ~~support claw portions 14~~wafer support portion 16 with the wafer makes the line contact, the region of the back surface of the wafer, which cannot be subjected to the film forming, can be reduced. Therefore, the distortion generated owing to the heat between the portion subjected to the film forming and the portion that is not subjected to the film forming on the back surface of the wafer can be reduced, and factors causing a damage to the wafer itself and the exfoliation of the film can be reduced.

Please replace the Abstract with the attached amended Abstract.